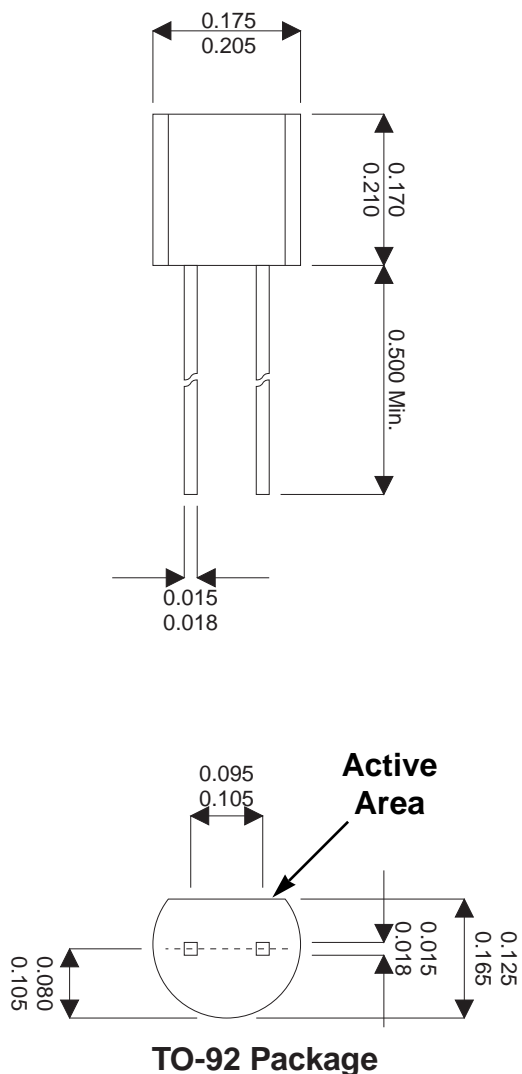


MECHANICAL DATA

Dimensions in inches.

**P.I.N. PHOTODIODE****FEATURES**

- WATER CLEAR PLASTIC
- WIDE SPECTRAL RESPONSE
- 0.1" (2.54mm) LEAD SPACING
- LOW DARK CURRENT

DESCRIPTION

The SMP400G-X1 is a silicon PIN photodiode which is incorporated in a colourless plastic package. The terminals are solder tabs with 0.1" (2.54mm) spacing. Due to its design the diode can be assembled vertically on PC board.

Arrays can be realised by multiple arrangements. This versatile photo detector can be used as a diode as well as a voltage cell.

The signal / noise ratio is particularly favourable, even at low illuminances.

The PIN photodiode is outstanding for low junction capacitance, high cut off frequency and short switching time. It is particularly suitable for IR sound transmission and remote control.

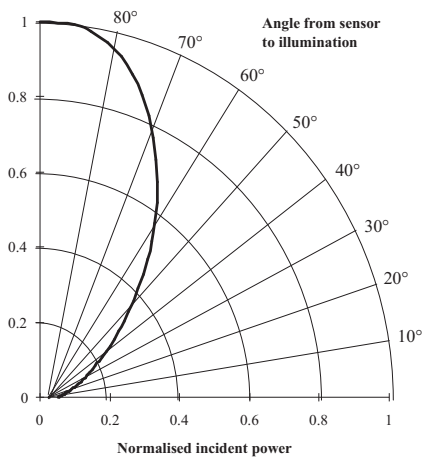
ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

| | |
|---|-----------------|
| Operating temperature range | -40°C to +70°C |
| Storage temperature range | -45°C to +80°C |
| Temperature coefficient of responsivity | 0.35% per °C |
| Temperature coefficient of dark current | x2 per 8°C rise |
| Reverse breakdown voltage | 60V |

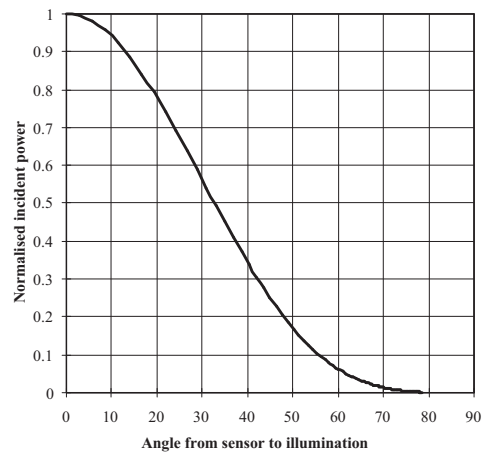
CHARACTERISTICS (T_{amb}=25°C unless otherwise stated)

| Characteristic | Test Conditions. | Min. | Typ. | Max. | Units |
|-------------------|-------------------------------|------|------|------|-----------------|
| Responsivity | λ at 900nm | 0.45 | 0.55 | | A/W |
| Active Area | | | 0.62 | | mm ² |
| Dark Current | E = 0 Dark 1V Reverse | | 0.1 | 1.0 | nA |
| | E = 0 Dark 10V Reverse | | 0.5 | 2.5 | |
| Breakdown Voltage | E = 0 Dark 10 μ A Reverse | 60 | 80 | | V |
| Capacitance | E = 0 Dark 0V Reverse | | 8 | 12 | pF |
| | E = 0 Dark 20V Reverse | | 1.5 | 2.5 | |
| Rise Time | 30V Reverse 50 Ω | | 4 | | ns |
| NEP | 900nm | | 7.2 | | W/ \sqrt Hz |

Directional characteristics



Directional Characteristics



Spectral Response

